



Experimental validation of a Bulk Built-In Current Sensor for detecting laser-induced current

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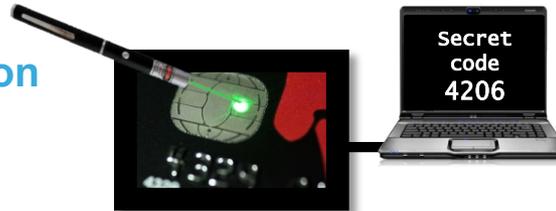


Introduction

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- Laser fault injection may be used to **alter a behavior** of an integrated circuit (IC)
 - e.g. **retrieve/modify** secret data in integrated circuit

Laser fault injection



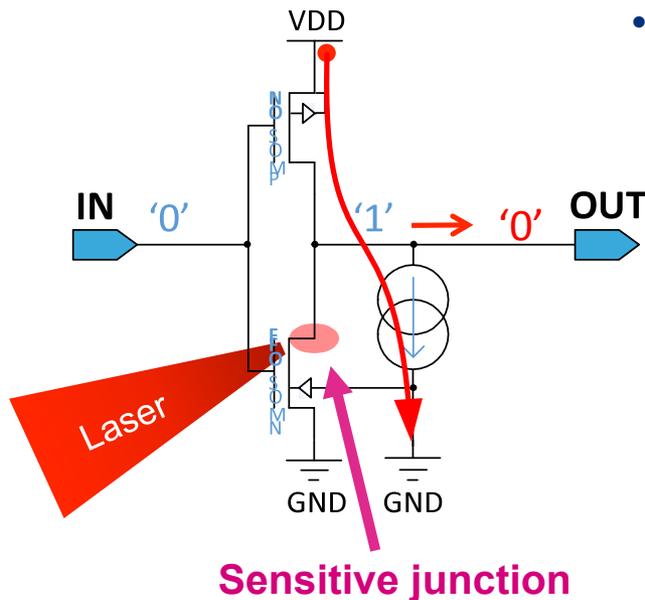
- Sensors are used to catch and flag when a perturbation appears
- **Bulk Built-In Current Sensors (BBICS)** were developed to detect the transient bulk currents induced in the bulk of ICs
- This presentation reports the experimental evaluation of a complete **BBICS architecture**, designed to simultaneously monitor **PMOS and NMOS wells**, under Photoelectric Laser Stimulation (**PLS**)



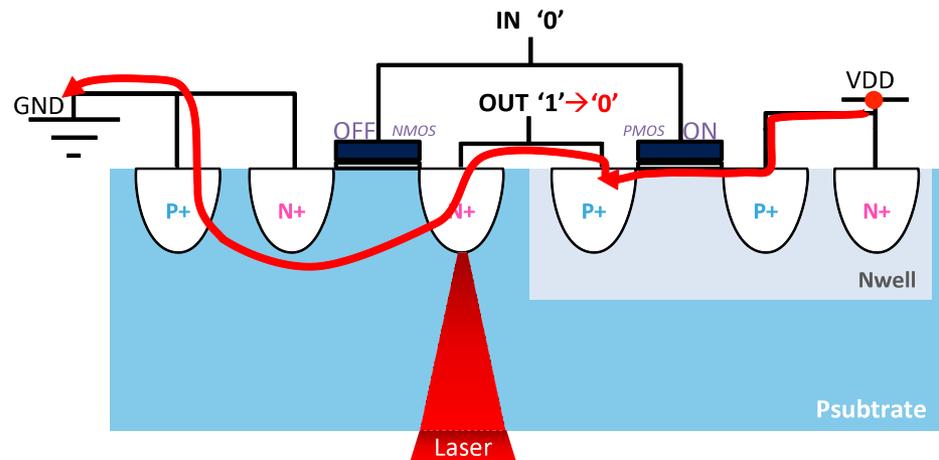
Single-Events Effects (SEE)

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- Example: Laser effect on a **CMOS inverter** with its input at low level
 - Photocurrent flows **through the Psubstrate**
 - Sensitive junction is the **Drain** of NMOS which is in OFF state



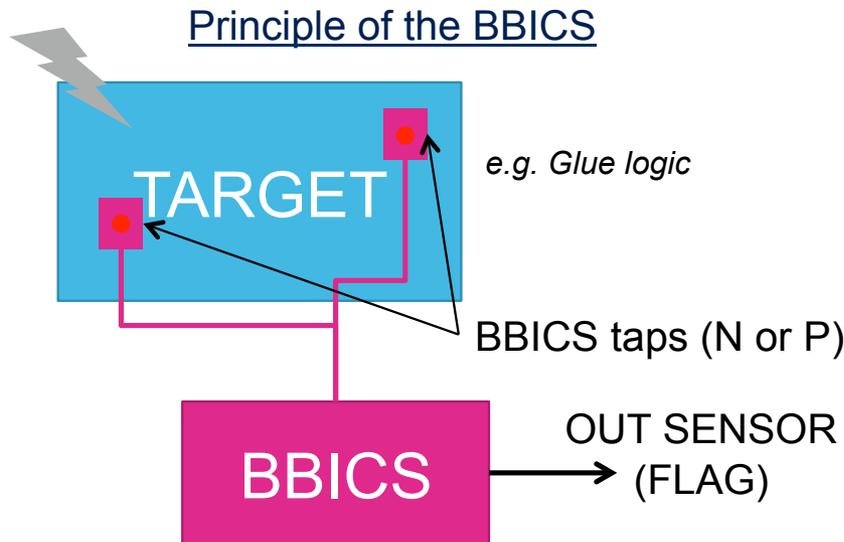
- State of the output from **'1' to '0'**
 - **Stuck-at fault**



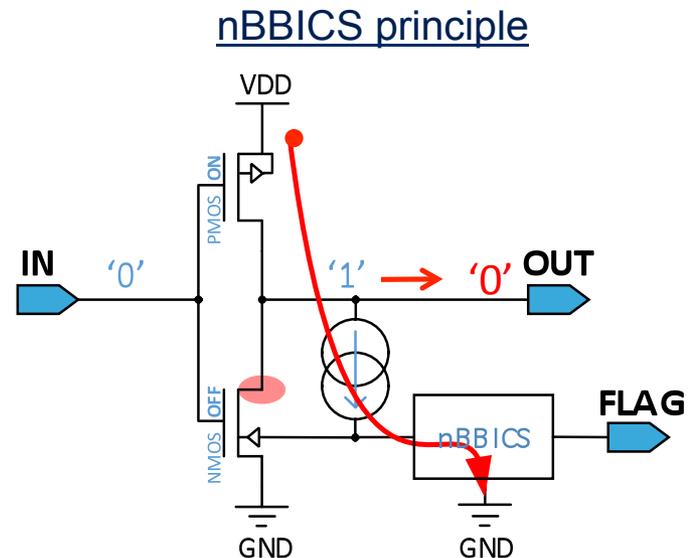


BBICS principles

- **BBICS** stands for **B**ulk **B**uilt-In **C**urrent **S**ensor
 - Principle : The BBICS detect all single-event transient currents in a target thanks to its different biasing taps in a target.



- BBICS **bias** the target
- BBICS **detect** the photocurrent flowing the BBICS taps

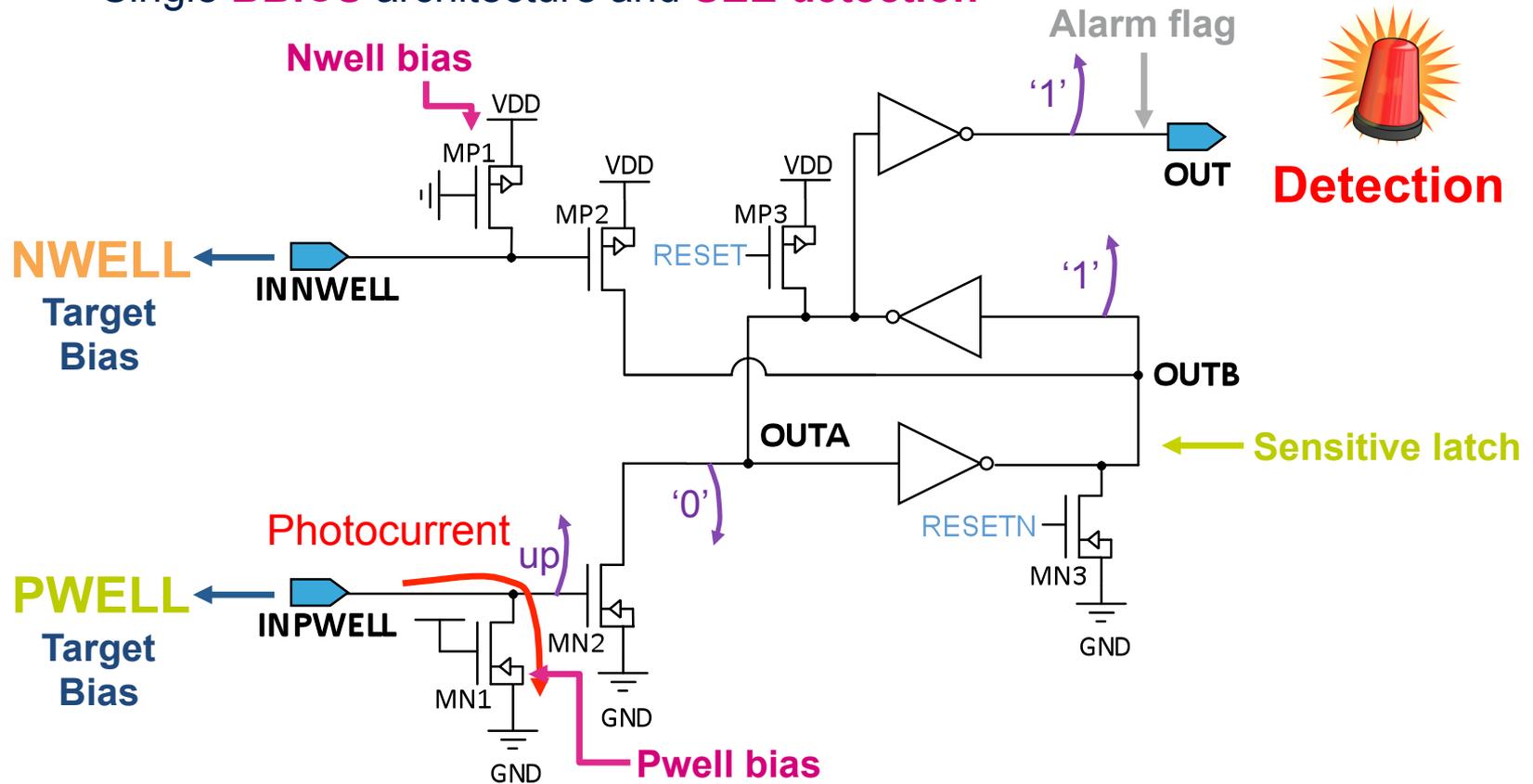


- Psubstrate **biased** through the nBBICS
- nBBICS **detects** the photocurrent flowing in the sensor



Architecture of the single BBICS used in experiments

- Single **BBICS** architecture and **SEE detection**

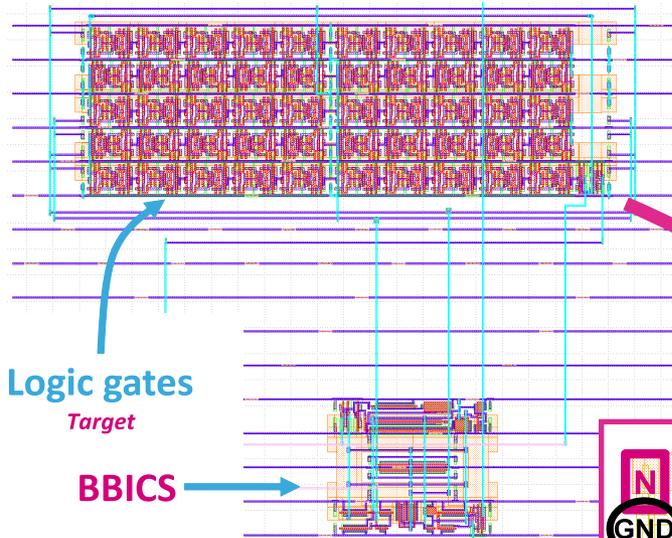


Detection

Sensitive latch

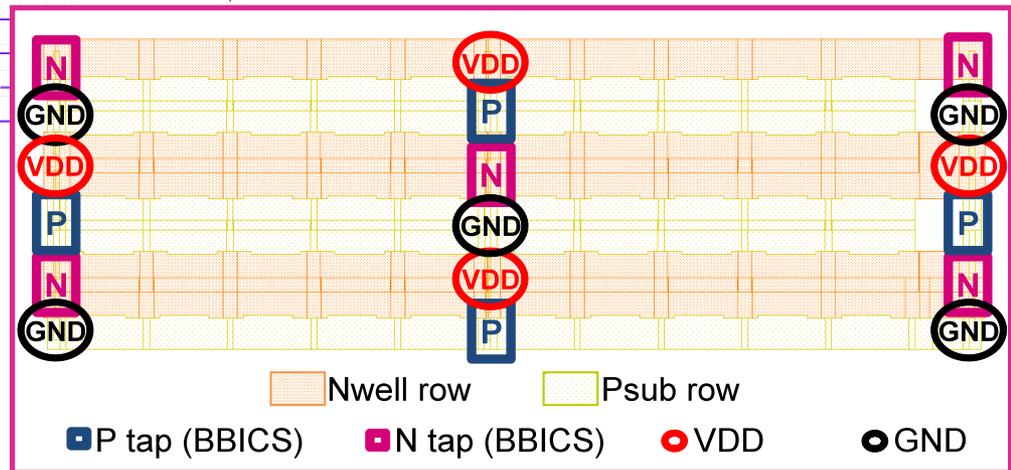


Layout distribution and tapping



- Classical well tapping
 - Nwell tapping at **1.2V**
 - Psub tapping at **0V**
- BBICS well tapping
 - **P taps** and **N taps**
- « Hybrid tapping » on target or 50%
 - **Merge** classical well tapping at power supply and BBICS tapping

- Target far from sensor
 - Avoid **perturbations** in the BBICS itself

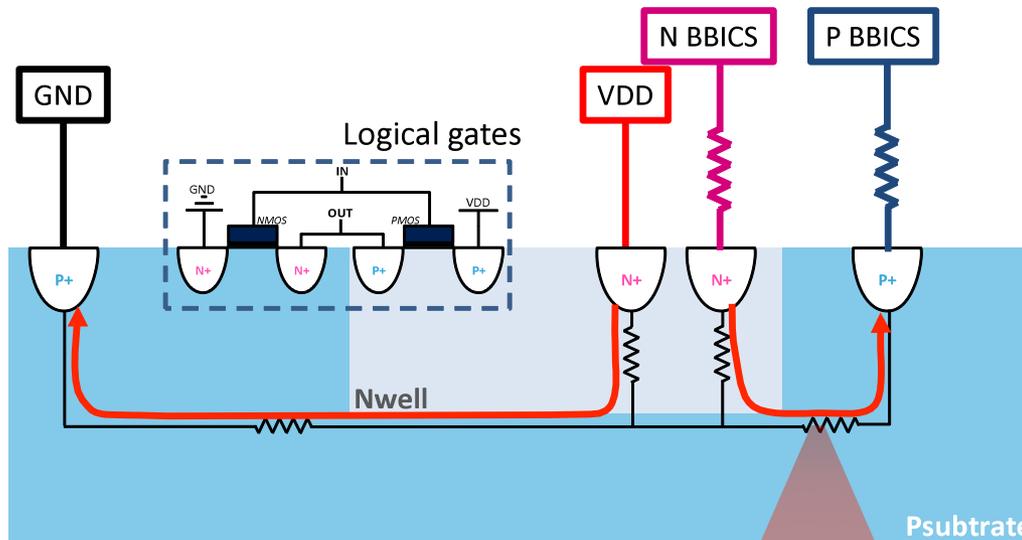




Theoretical hypothesis

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- Experimental hypothesis
 - Photocurrents flowing from VDD to GND may follow **two paths**
 - Photocurrent will **choose the less resistive path** depending on the position



Resistors
VDD or GND < BBICS

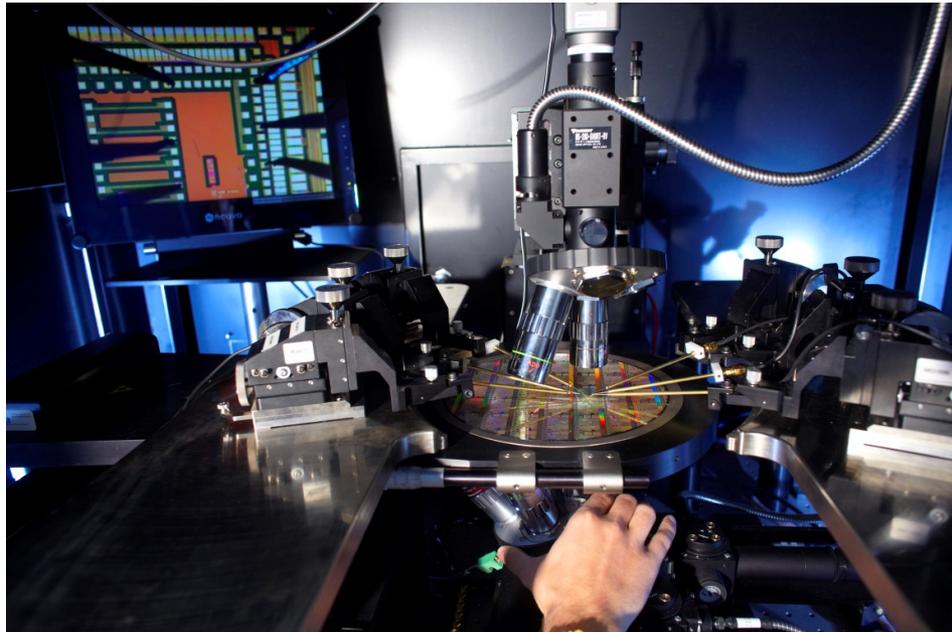
- Less resistive **VDD/VDD path** compared to BBICS taps
- **No detection** close to VDD/GND

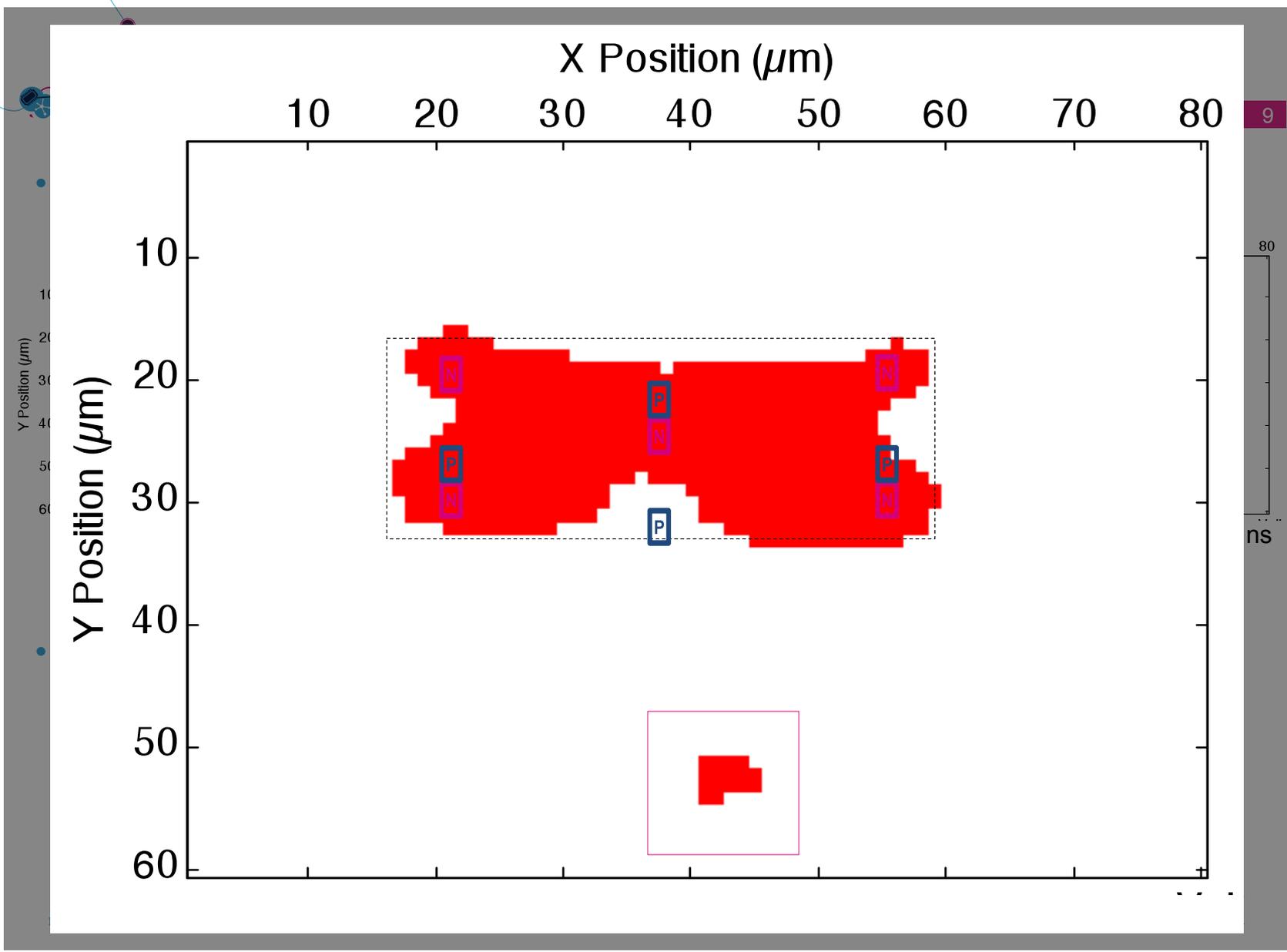


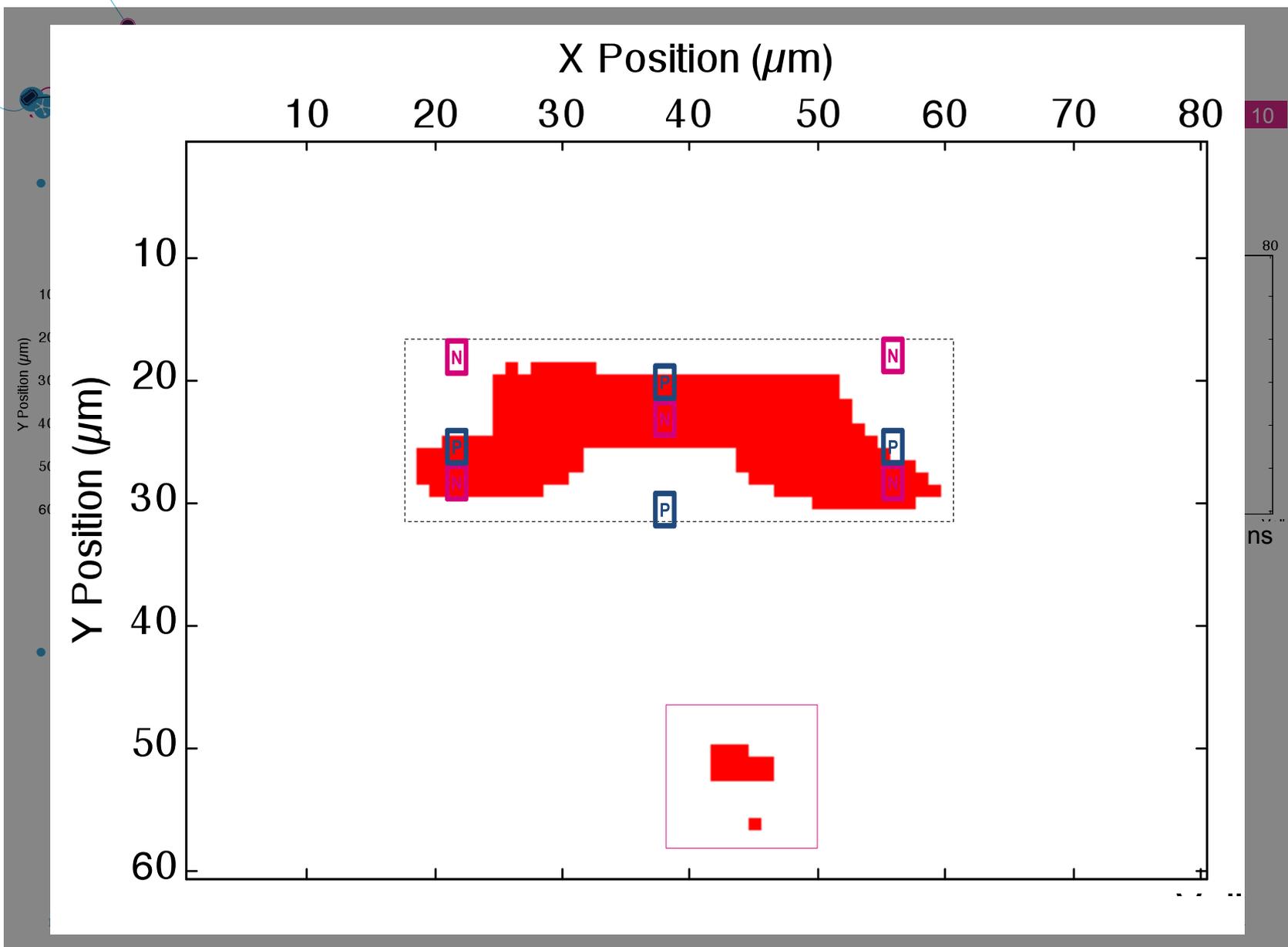
Experiments 8

- Experimental set up

- Wavelength: **1064 nm** (near Infra Red)
- Spot size: **~ 1 μ m**
- Laser through silicon substrate **backside**
- Laser power: **300 mW** and **250 mW**
- Laser pulse duration: **200 ns**, **100 ns** and **50 ns**





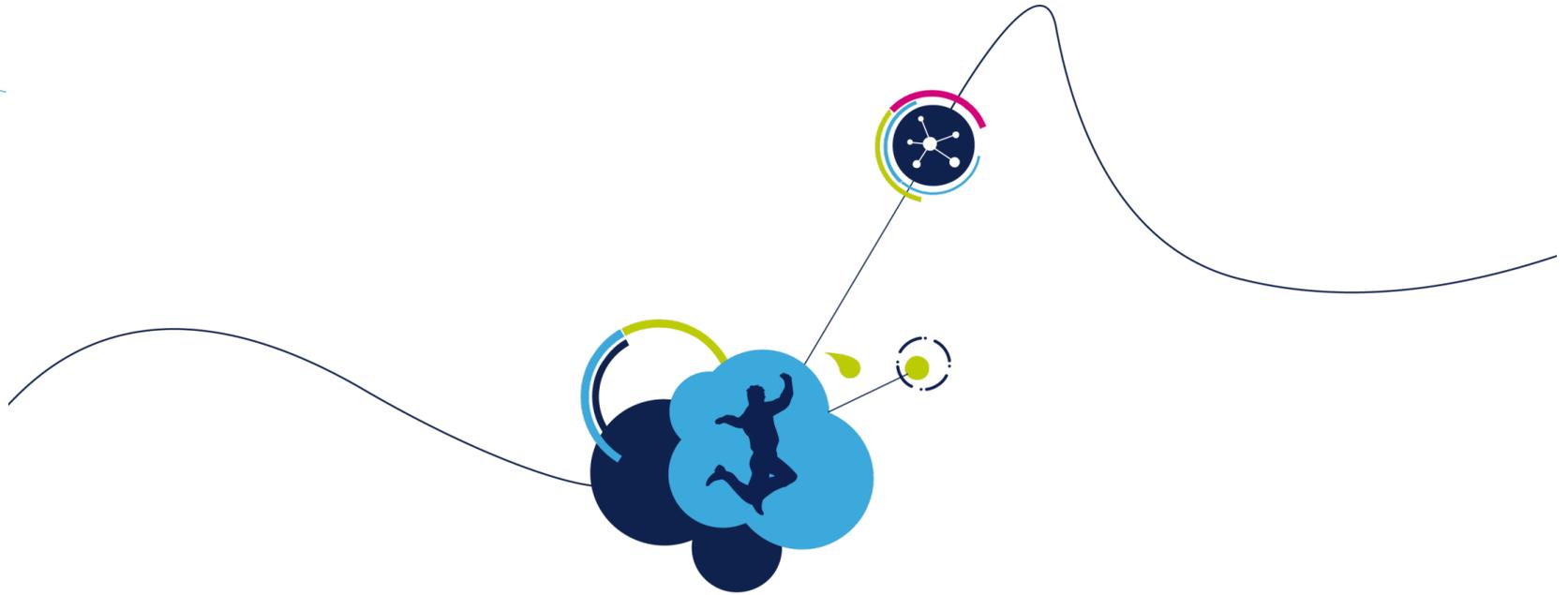




Conclusion and perspectives

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- The detection is **effective** for long laser pulse durations close to **N and P taps couples** but fail for short pulses duration
- **Detection effective** close to **BBICS taps couples**
- **No detection everywhere** because of the **hybrid tapping**
 - The classical biasing (VDD and GND) **hide** the BBICS detection
- Perspectives and future works
 - **New BBICS** will be designed and tested to validate other tapping (**100% BBICS taps**)



Thank you for your attention

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